



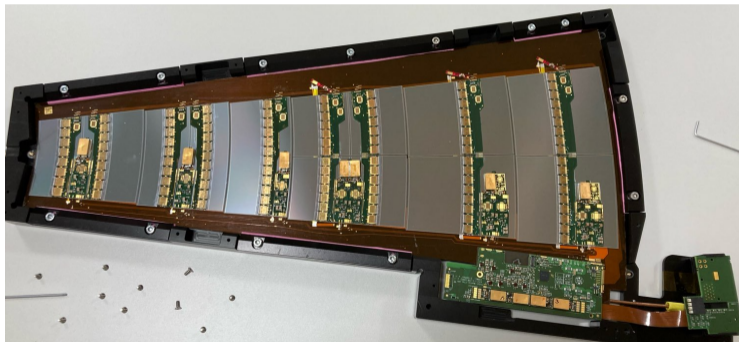
## Performance of Stitched Passive CMOS Strip Sensors

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# Motivation

## Why passive CMOS detectors?

- ▶ Large area detectors are limited to microelectronics foundries
- ▶ This project wants to study the production of strip sensors in a CMOS foundry

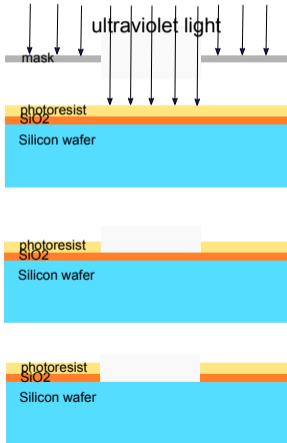


Picture of the petal, ATLAS endcap substructure. The silicon strip sensors have an area around  $10 \times 10 \text{ cm}^2$

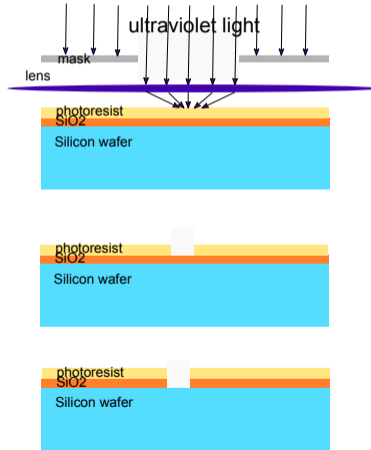
# What changes regarding microelectronic foundries?

## Photolithography

### Microelectronics photolithography



### CMOS photolithography



### Semiconductor device fabrication



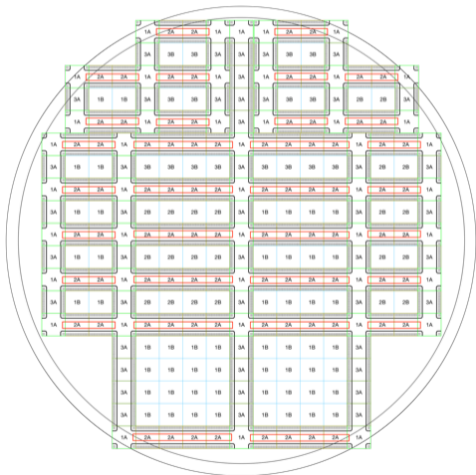
### MOSFET scaling (process nodes)

- 10  $\mu\text{m}$  – 1971
- 6  $\mu\text{m}$  – 1974
- 3  $\mu\text{m}$  – 1977
- 1.5  $\mu\text{m}$  – 1981
- 1  $\mu\text{m}$  – 1984
- 800 nm – 1987
- 600 nm – 1990
- 350 nm – 1993
- 250 nm – 1996
- 180 nm – 1999
- 130 nm – 2001
- 90 nm – 2003
- 65 nm – 2005
- 45 nm – 2007
- 32 nm – 2009
- 22 nm – 2012
- 14 nm – 2014
- 10 nm – 2016
- 7 nm – 2018
- 5 nm – 2020
- Future
- 3 nm ~ 2022
- 2 nm ~ 2023

[Image from wikipedia]

# Passive CMOS strips

## Mask for passive CMOS fabrication



## Passive CMOS strips project

- ▶ Collaboration with Uni Freiburg, Uni Bonn and DESY



- ▶ Fabricated in LFoundry with 150 nm
- ▶ It has strip and pixel sensors (pixel presentation by Yannick Dieter)
- ▶ Reticles are around  $1\text{ cm}^2$
- ▶ 1A and 2A are the strip (1A is the bottom and top of the strip)
- ▶ Strips are  $2\text{ cm}^2$  and  $4\text{ cm}^2$  long

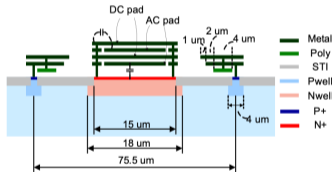
# Strip designs. Sensors have two flavours (actually they are 3)

## Regular implant

Strip 2



- Coupling with parasitic capacitance
  - Parallel metal plate
  - 1<sup>st</sup> metal and N implant



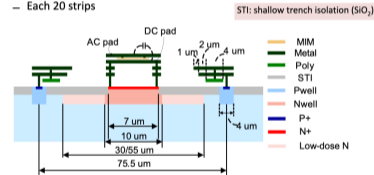
- ▶ Wafer is 150 μm thick
- ▶ There are 2 strip sensors which 40 strips each
  1. 40 regular implant strips
  2. 40 low dose implant strips (20 strips with 30 μm and 20 strips with 55 μm)

## Low dose implant

Strip 1

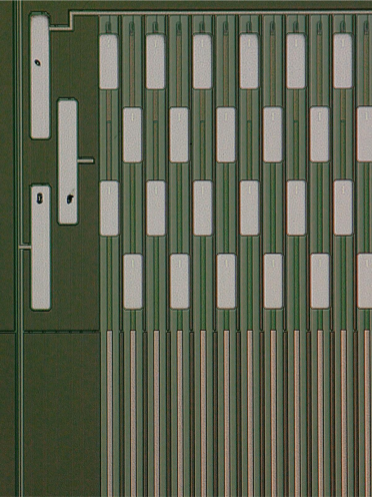


- Coupling with MIM (metal-insulator-metal) capacitor
  - Between MIM layer and 3<sup>rd</sup> metal
- 2 different Low-dose N implant width: 30 or 55 μm
  - 3.5 MeV implant with 10<sup>11</sup> doping concentration
  - Each 20 strips

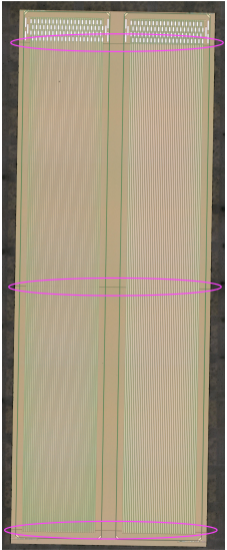
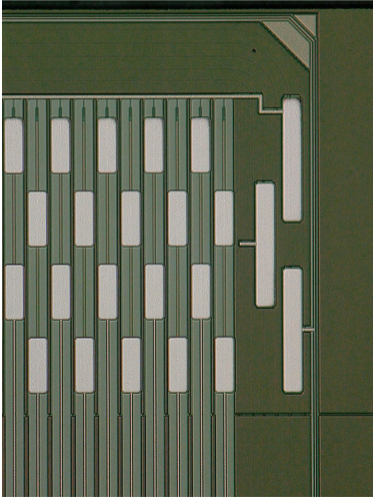


# Pictures of the stitching

Regular implant

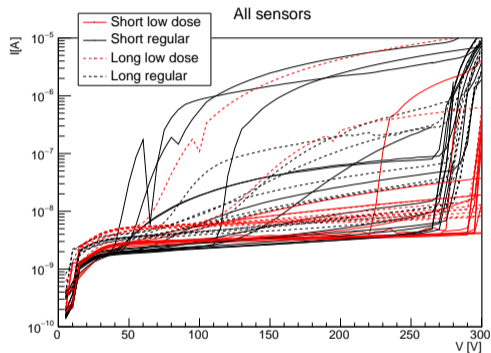


Low dose implant

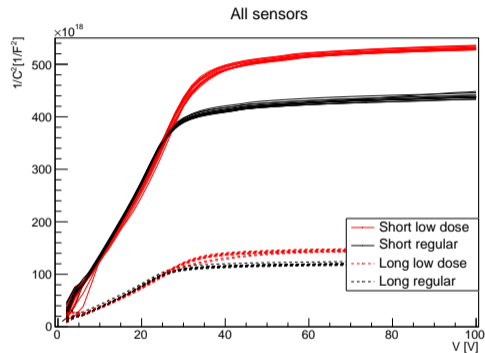


# IV and CVs

## IV curve



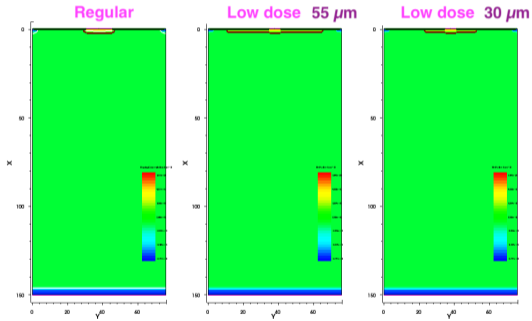
## CV curve



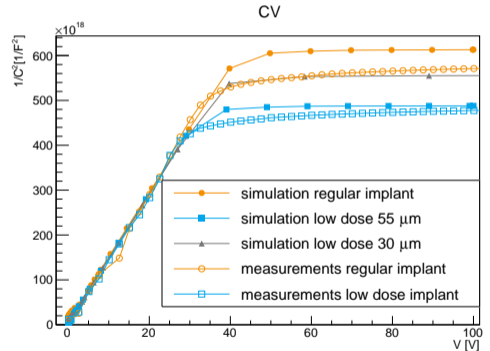
- ▶ The detectors show good electrical performance till breakdown 300 V
- ▶ Due to differences of the strips, they show differences with the CVs
- ▶ They have full depletion at 30 V and 36 V

# TCAD simulations

## Doping



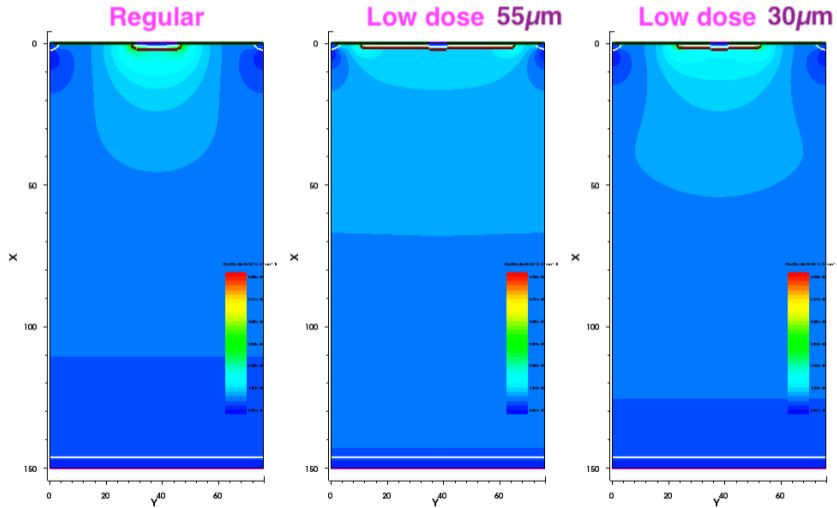
## CV comparison





# TCAD simulation

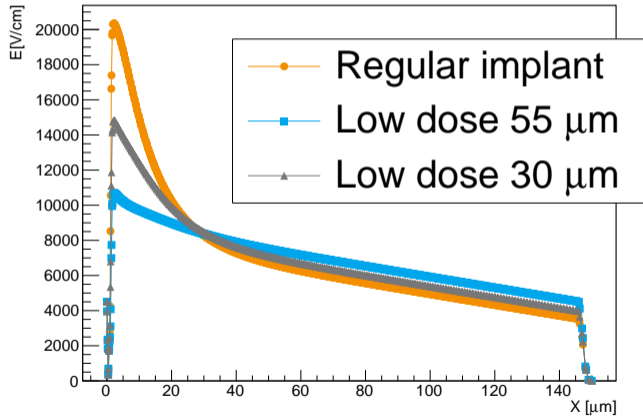
## Electric field



# TCAD simulation

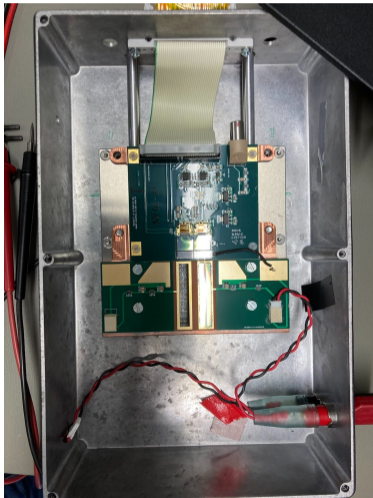
## Electric field at 100 V

Electric field in the center of the strip

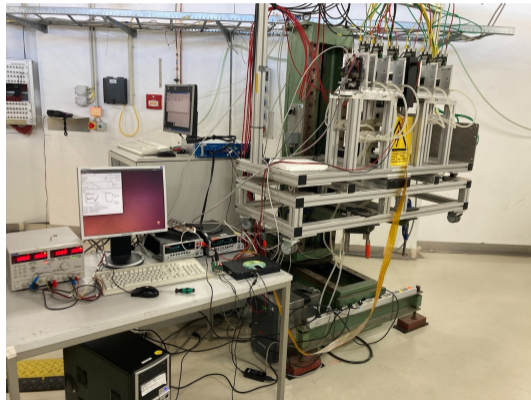


# Testbeam at DESY (done in April 2021)

## Sensor setup with ALiBaVa



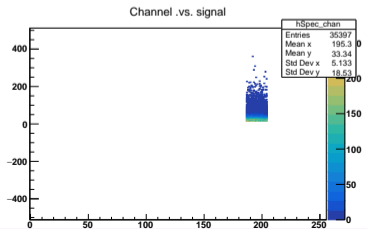
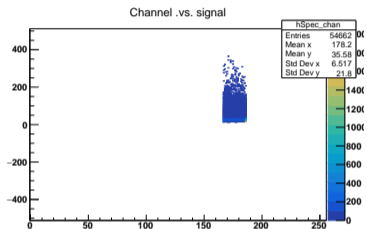
## Testbeam at DESY (TB22)



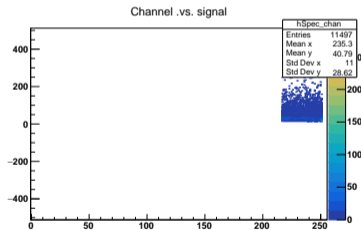
# Output from alibava at 100 V

The channels are separated for the three different sensor flavours

## Low dose implant (separated 20 strips)



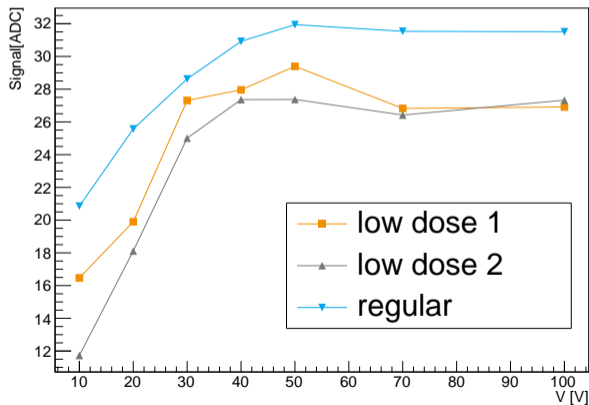
## Regular implant



# Preliminary results of testbeam Alibava data

DESY testbeam (using 4.6 GeV electrons)

Alibava signal (Preliminary), not including telescope data



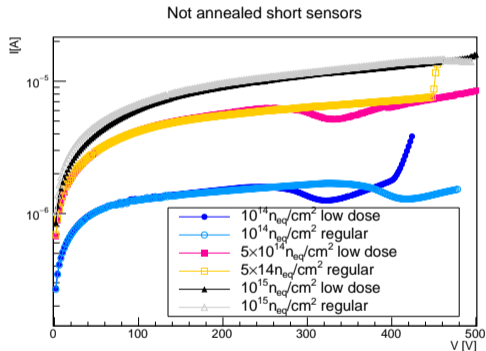
## Preliminary results

- ▶ Regular and low dose implant have different signal, calibration needs to be done
- ▶ Full reconstruction of the testbeam data ongoing

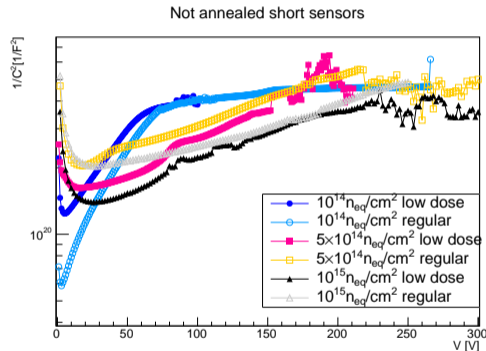
# Short sensors irradiated with protons at KIT ( 23 MeV)

Measured at  $-20^{\circ}\text{C}$

IV



CV at 1 kHz



- ▶ Annealing steps needs to be followed but they show good behaviour after irradiation
- ▶ Freiburg University colleagues are investigating neutron irradiated samples

# Future steps

## Conclusions

- ▶ No negative effects from stitching so far, first IV's and CV's after irradiation do not show any problem

## Future steps

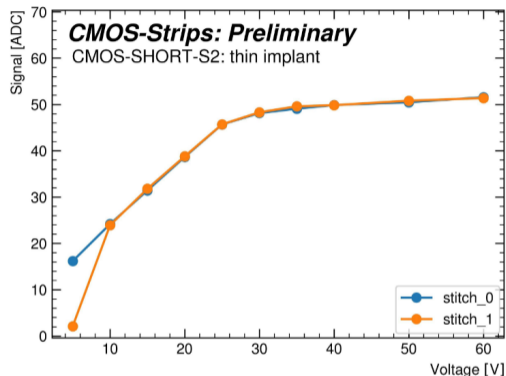
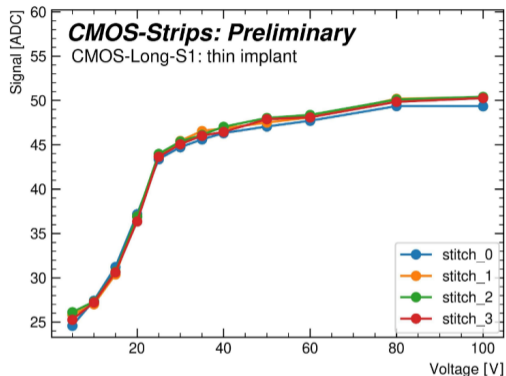
- ▶ Further electrical studies of the irradiated samples
- ▶ Test with a radioactive source
- ▶ Testbeam with the irradiated sensors

The measurements leading to these results have been performed at the Test Beam Facility at DESYHamburg (Germany), a member of the Helmholtz Association (HGF).

backup



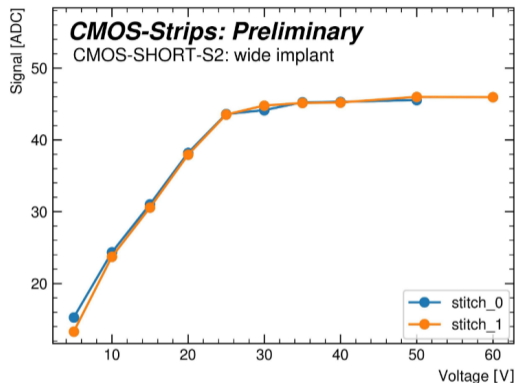
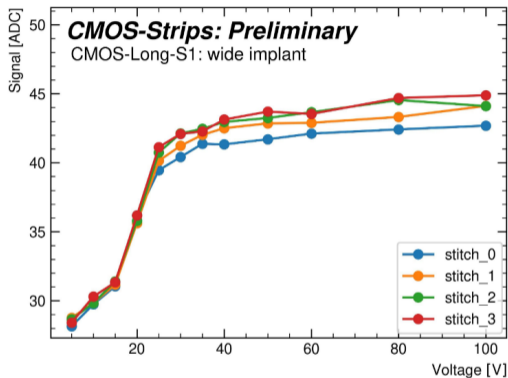
# Alibava measurements regular sensor



[Arturo Rodriguez, Trento meeting 2021]

- ▶ Measurements taken with an ALiBaVa setup with  $\text{Sr}^{90}$  source at 4 different stitching points of the sensors
- ▶ No effect of stitching

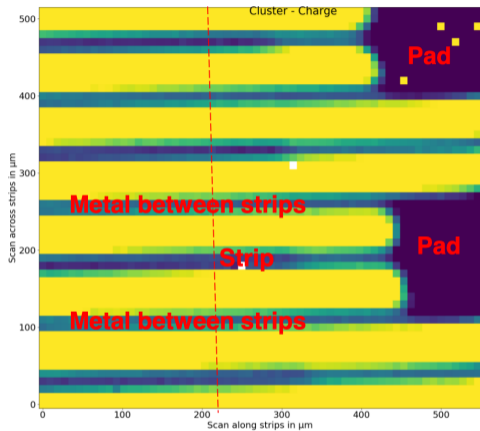
# Alibava measurements low dose



[Arturo Rodriguez, Trento meeting 2021]

- Probably some difference due to higher noise of the sensor (noise plot in backup slides)

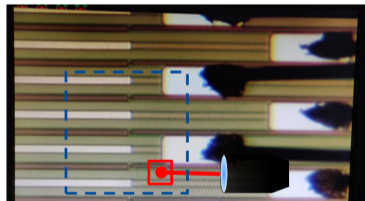
# TCT measurements



First measurement to check stitch @ 50 V

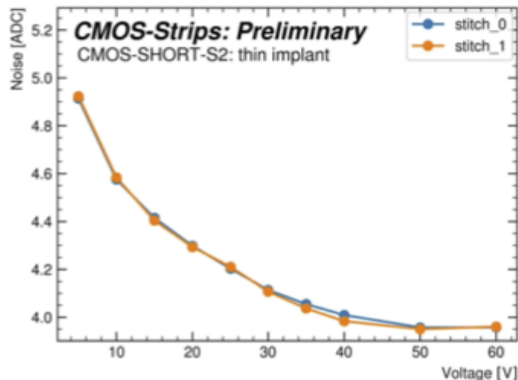
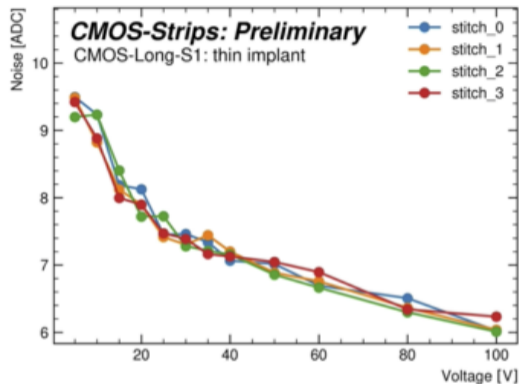
UN  
FRE

Due to the metallization (blue horizontal lines): results are only hints



[Cedric Hoenig, RD50 2020]

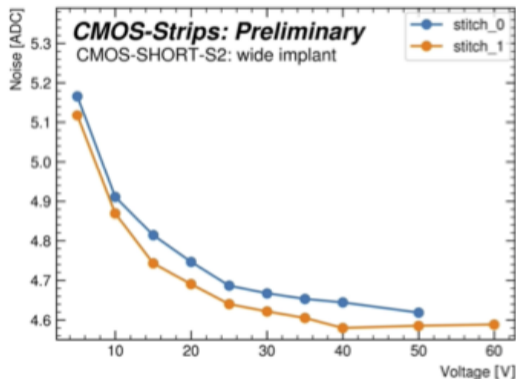
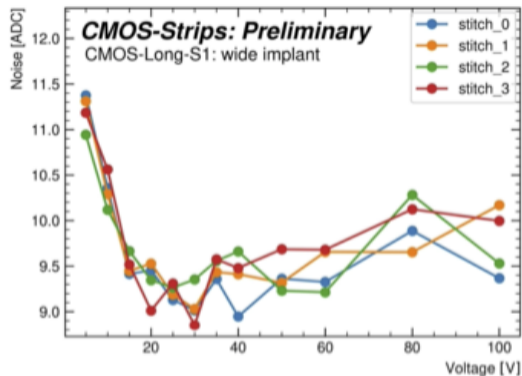
## Alibava measurements → Noise



- ▶ No effect of stitching

[Arturo Rodriguez, Trento meeting 2021]

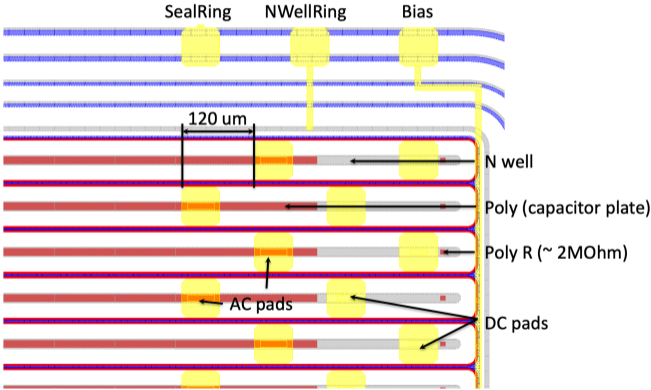
## Alibava measurements → Noise



- ▶ More difference in the regions, maybe due to higher noise  
[Arturo Rodriguez, Trento meeting 2021]

# Strips layout

## Strip design – pad



1/22/2019

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# CV measurement with frequency

